



SHANGHAI SUNRISE ELECTRONICS CO., LTD.

SB820 THRU SB860

SCHOTTKY BARRIER RECTIFIER

TECHNICAL SPECIFICATION

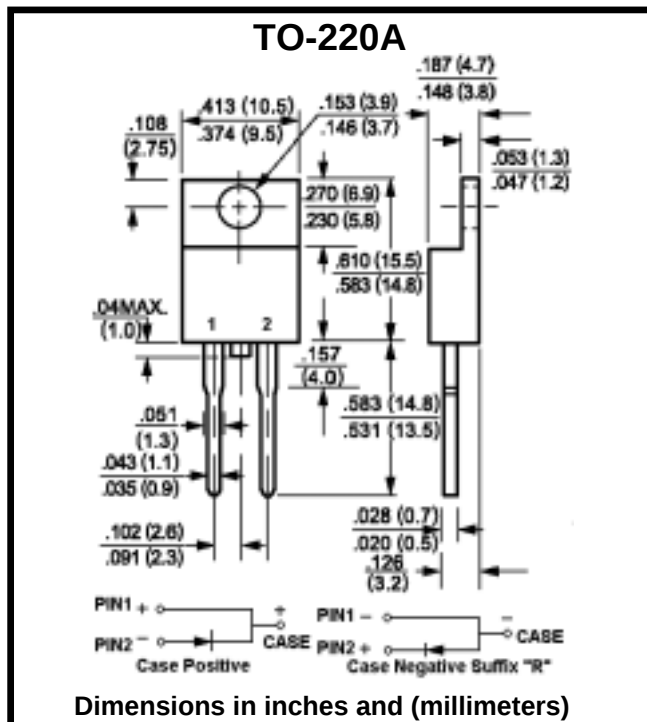
VOLTAGE: 20 TO 60V CURRENT: 8.0A

FEATURES

- Epitaxial construction for chip
- High current capability
- Low forward voltage drop
- Low power loss, high efficiency
- High surge capability
- High temperature soldering guaranteed:
250°C/10sec/0.375"(9.5mm) lead length
at 5 lbs tension

MECHANICAL DATA

- Terminal: Plated leads solderable per
MIL-STD 202E, method 208C
- Case: Molded with UL-94 Class V-O
recognized flame retardant epoxy
- Polarity: As marked
- Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	SB 820	SB 830	SB 835	SB 840	SB 850	SB 860	UNITS
Maximum Repetitive Peak Reverse Voltage	V _{RRM}	20	30	35	40	50	60	V
Maximum RMS Voltage	V _{RMS}	14	21	25	28	35	42	V
Maximum DC Blocking Voltage	V _{DC}	20	30	35	40	50	60	V
Maximum Average Forward Rectified Current (T _C =95°C)	I _{F(AV)}	8.0						A
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	I _{FSM}	150						A
Maximum Forward Voltage (at 8.0A DC)	V _F	0.65				0.75		V
Maximum DC Reverse Current T _a =25°C (at rated DC blocking voltage) T _a =100°C	I _R	5.0 50.0						mA mA
Typical Junction Capacitance (Note 1)	C _J	700				450		pF
Typical Thermal Resistance (Note 2)	R _{θ(ja)}	2.5						°C/W
Operating Junction Temperature	T _J	-65 to +125				-65 to +150		°C
Storage Temperature	T _{STG}	-65 to +150						°C

Note:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0Vdc
2. Thermal resistance from junction to case
3. Suffix "R" for reverse polarity

<http://www.sse-diode.com>